

Docket No.: 61352-051



**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
Yoshiaki HASEGAWA, et al.	:	Confirmation Number: 4412
Serial No.: 10/687,647	:	Group Art Unit: 2811
Filed: October 20, 2003	:	Examiner: Unknown
For: METHOD FOR FABRICATING SEMICONDUCTOR LIGHT EMITTING DEVICE		

**INFORMATION DISCLOSURE STATEMENT**

Honorable Commissioner for Patents and Trademarks  
Washington, D. C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed with the application and no certification or fee is required.

The relevance of the references listed on attached Form 1449 is discussed in the present specification.

Japanese Unexamined Publication P2001-244560A was cited by the Inventors.

A copy of the foreign search report is attached for the Examiner's information.

Please note this is a PCT application in the entry of the National Phase in the U.S. and

copies of the references cited were transmitted by WIPO and are believed to be in the file of the above identified application and readily available to the Examiner. However, to ensure that these references are available to the Examiner, we are providing copies of these references herewith. Since the Search Report was from the U.S. JPO or EPO search authorities, copies of these references should have been supplied to the USPTO under the trilateral agreement and are believed to be in the file of the above identified application and readily available to the Examiner. Therefore it is believed that Applicants have met all requirements regarding duty of disclosure under 37 CFR 1.56. Acknowledgement and consideration of these documents are respectfully requested.

Respectfully submitted,

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**Date: February 11, 2004**

<b>INFORMATION DISCLOSURE</b> <b>CITATION IN AN</b> <b>APPLICATION</b>  (PTO-1449)				ATTY. DOCKET NO. <b>61352-051</b>		SERIAL NO. <b>10/687,647</b>	
				APPLICANT <b>Yoshiaki HASEGAWA, et al.</b>			
				FILING DATE <b>October 20, 2003</b>		GROUP <b>2811</b>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		US 5,757,833	05/26/1998	Arakawa et al.		Corresponds to JP 9-191150	
		US					
		US					
		US					
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number 4 - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP P2001-244560A	09/07/2001	SONY CORP		(Japan w/English Abstract)	
		JP P2000-196188A	07/14/2000	TOSHIBA CORP		(Japan w/English Abstract)	
		JP 9-191150	07/22/1997		Corresponds to US 5,757,833		
		JP 63-1370	01/07/1988	SANYO ELECTRIC CO., LTD.		(Front page of Japanese Patent and English Abstract)	
		JP 63-34992	02/15/1988	NEC CORP		(Japan w/English Abstract)	
		JP 5-343813	12/24/1993	ASAHI GLASS CO LTD		(Japan w/English Abstract)	
		JP 5-259079	10/08/1993	NEC CORP		(Japan w/English Abstract)	
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		Shuji NAKAMURA, "InGaN Multiquantum-Well-Structure Laser Diodes with GaN-AlGaIn Modulation-Doped Strained-Layer Superlattices", IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No. 3, May/June 1998, p. 483-489					
		H. MARCHAND, et al., "Mechanisms of Lateral Epitaxial Overgrowth of Gallium Nitride by Metalorganic Chemical Vapor Deposition", Journal of Crystal Growth, 195 (1998) 328-332					
		Michael KNEISSL, et al., "Performance and Degradation of Continuous-wave InGaIn Multiple-Quantum-Well Laser Diodes on Epitaxially Laterally Overgrown GaN Substrates", Applied Physics Letters, Vol. 77, No. 13, September 25, 2000, pages 1931-1933					
		Shuji NAKAMURA, "UV/Blue/Green InGaIn-Based LEDs and Laser Diodes Grown on Epitaxially Laterally Overgrown GaN", IEICE Trans. Electron., Vol. E83-C, No. 4, April 2000, p. 529-535					
		Shuji NAKAMURA, et al., "InGaIn/GaN/AlGaIn-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices Grown on an Epitaxially Laterally Overgrown GaN Substrate", Applied Physics Letters, Vol. 72, No. 2, pages 211-213 (1998)					
EXAMINER				DATE CONSIDERED			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.